2N5401

Amplifier Transistors

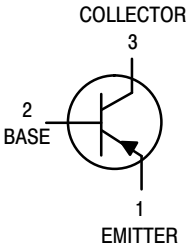
PNP Silicon

Features

- These are Pb−Free Devices*

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MAXIMUM RATINGS

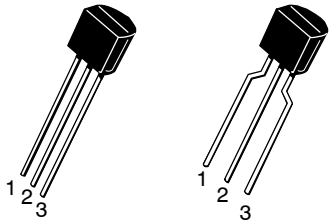
Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	150	Vdc
Collector − Base Voltage	V_{CBO}	160	Vdc
Emitter − Base Voltage	V_{EBO}	5.0	Vdc
Collector Current − Continuous	I_C	600	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

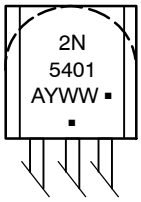
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

TO−92
CASE 29
STYLE 1



MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Breakdown Voltage (Note 1) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	150	–	Vdc
Collector−Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	160	–	Vdc
Emitter−Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	–	Vdc
Collector Cutoff Current (V_{CB} = 120 Vdc, I_E = 0) (V_{CB} = 120 Vdc, I_E = 0, T_A = 100°C)	I_{CBO}	– –	50 50	nAdc μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)	I_{EBO}	–	50	nAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain (I_C = 1.0 mAdc, V_{CE} = 5.0 Vdc) (I_C = 10 mAdc, V_{CE} = 5.0 Vdc) (I_C = 50 mAdc, V_{CE} = 5.0 Vdc)	h_{FE}	50 60 50	– 240 –	–
Collector−Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	– –	0.2 0.5	Vdc
Base−Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc) (I_C = 50 mAdc, I_B = 5.0 mAdc)	$V_{BE(sat)}$	– –	1.0 1.0	Vdc
SMALL−SIGNAL CHARACTERISTICS				
Current−Gain — Bandwidth Product (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	100	300	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	6.0	pF
Small−Signal Current Gain (I_C = 1.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	h_{fe}	40	200	–
Noise Figure (I_C = 250 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 kΩ, f = 1.0 kHz)	NF	–	8.0	dB

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device	Package	Shipping†
2N5401G	TO−92 (Pb−Free)	5000 Unit / Bulk
2N5401RLRAG	TO−92 (Pb−Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

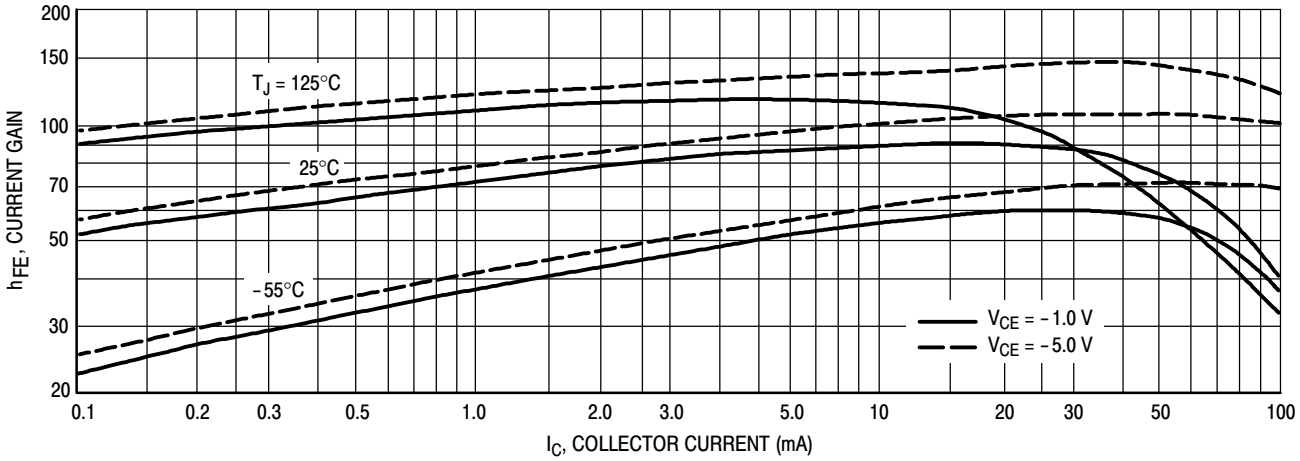


Figure 1. DC Current Gain

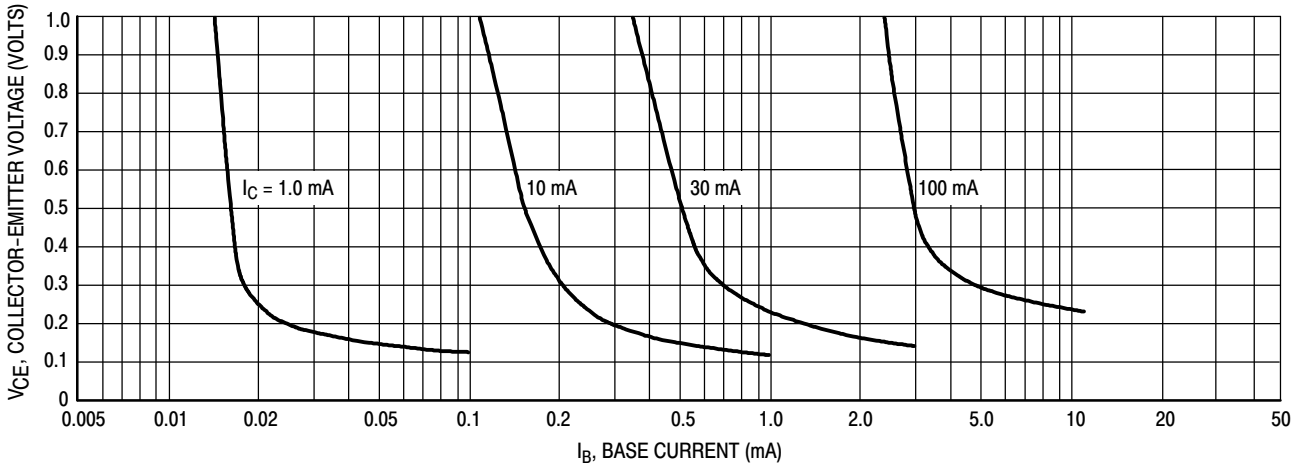


Figure 2. Collector Saturation Region

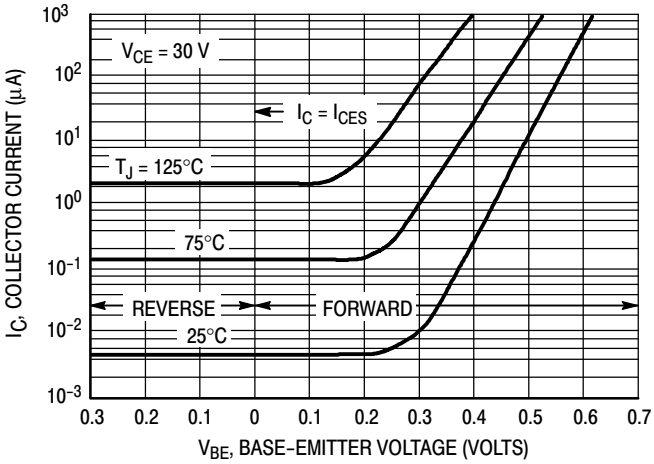


Figure 3. Collector Cut−Off Region

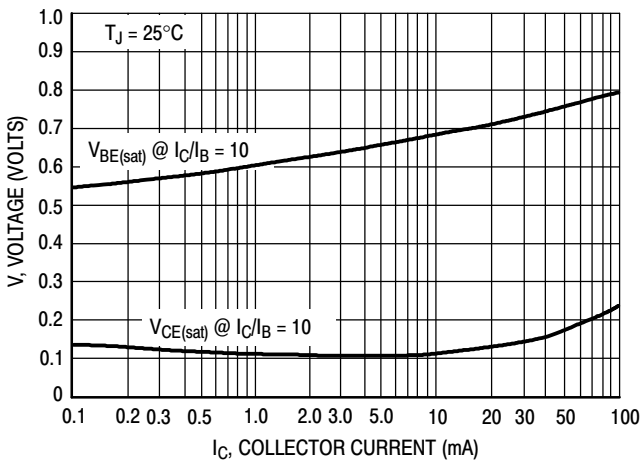


Figure 4. “On” Voltages

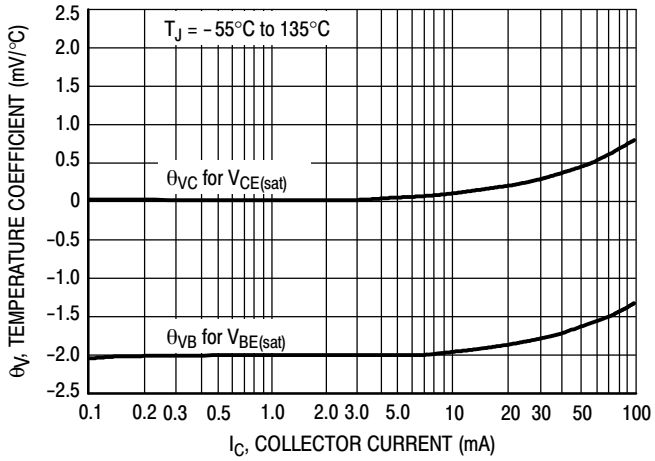
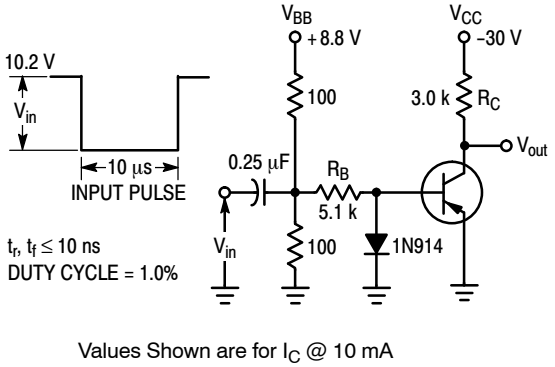


Figure 5. Temperature Coefficients



Values Shown are for I_C @ 10 mA

Figure 6. Switching Time Test Circuit

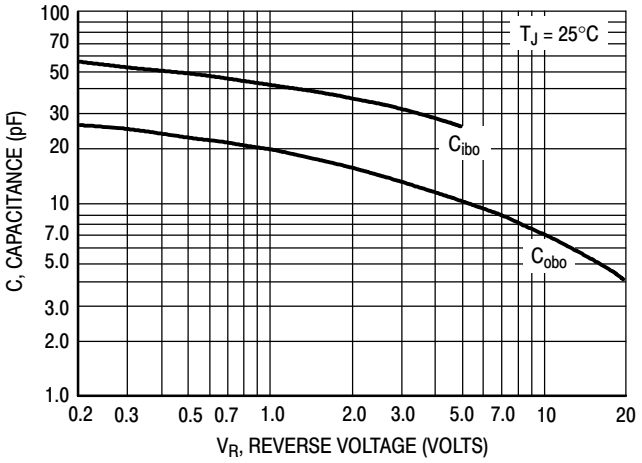


Figure 7. Capacitances

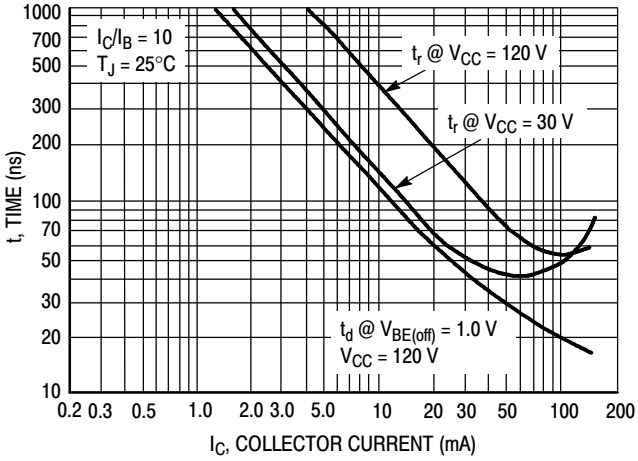


Figure 8. Turn−On Time

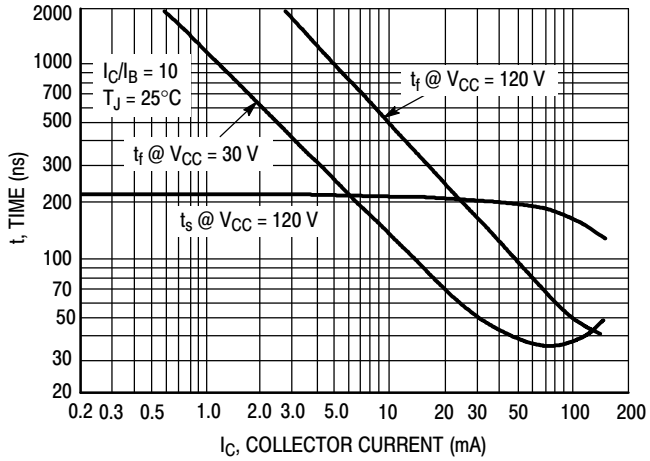


Figure 9. Turn−Off Time

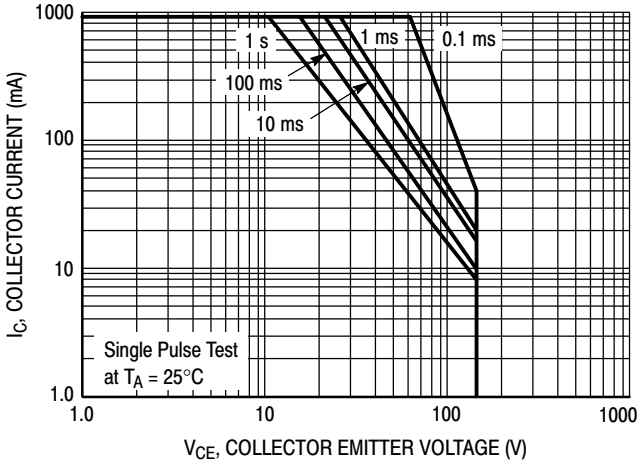
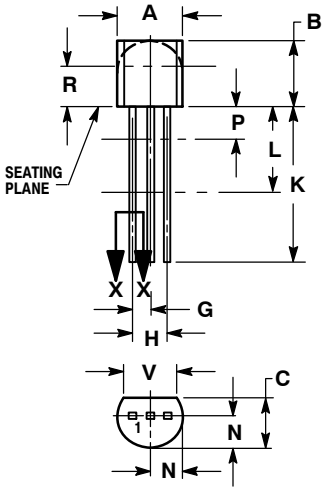


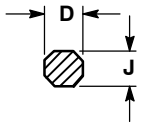
Figure 10. Safe Operating Area

PACKAGE DIMENSIONS

TO−92 (TO−226)
CASE 29−11
ISSUE AM



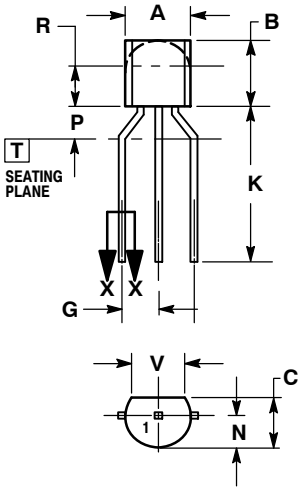
STRAIGHT LEAD
BULK PACK



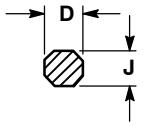
SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS	
DIM	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

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